MSKSEMI 美森科







TVC



TSS



MOV



GDT



DIED

MURAXXXT3G-MS

Product specification





SURFACE MOUNT ULTRAFAST POWER RECTIFIERS DIODES

VOLTAGE RANGE: 50 - 600V

CURRENT: 1.0 A

Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop, High Efficiency
- Low Power Loss
- Super-Fast Recovery Time
- Plastic Case Material has UL Flammability Classification Rating 94V-O

Mechanical Data

- Case: SMA/DO-214AC, Molded Plastic
- Terminals: Solder Plated, Solderable
- per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Weight: 0.064 grams (approx.)

Reference News

PACKAGE OUTLINE	Marking
	MURA ***
SMA(DO-214AC)	*** Representative VRRM



Maximum Ratings and Electrical Characteristics TA = 25℃ unless otherwise specified Single

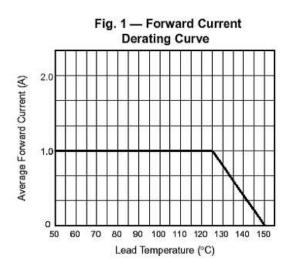
phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

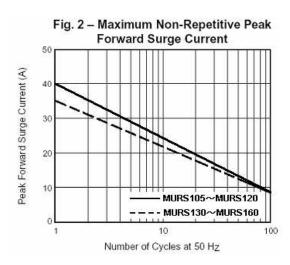
Characteristic	Symbol	MURA105 T3G-MS	MURA110 T3G-MS	MURA115T 3G-MS	MURA120 T3G-MS	MURA130T 3G-MS	MURA140 T3G-MS	MURA160T 3G-MS	Unit
Maximum repetitive peak reverse voltage	Vrrm	50	100	150	200	300	400	600	V
Maximum RMS voltage	VRMS	35	70	105	140	210	280	420	V
Maximum DC blocking voltage	VDC	50	100	150	200	300	400	600	V
Maximum average forward rectified current at TL=55 ℃	l(AV)	1.0					А		
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	Ігѕм	30.0			А				
Maximum instantaneous forward voltage at 1.0A	VF			0.95		1	.25	1.7	V
Maximum DC reverse current $T_{A=25}^{\circ}$ at rated DC blocking voltage $T_{A=100}^{\circ}$	lR	5.0 50.0			μΑ				
Maximum reverse recovery time (NOTE 1)	trr	35			ns				
Typical junction capacitance (NOTE 2)	Сл	15.0			pF				
Typical thermal resistance (NOTE 3)	Rθja	60.0			°C/W				
Operating junction and storage temperature range	ТЈ,Тѕтс	-50 to +150				°C			

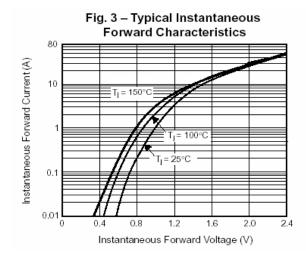
Note:1.Reverse recovery condition IF=0.5A,IR=1.0A,Irr=0.25A 2.Measured at 1MHz and applied reverse voltage of 4.0V D.C. 3.P.C.B. mounted with 0.2x0.2"(5.0x5.0mm) copper pad areas

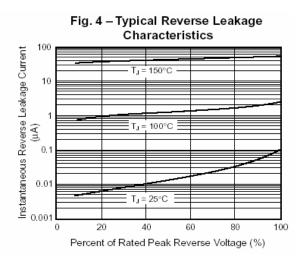


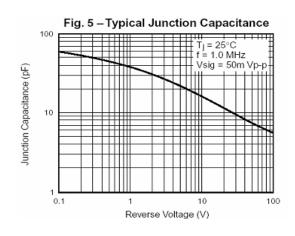
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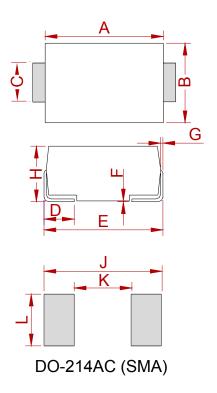








PACKAGE MECHANICAL DATA



	Dimensions				
Ref.	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
Α	4.25	4.65	0.167	0.183	
В	2.50	2.90	0.098	0.114	
С	1.35	1.65	0.053	0.065	
D	0.76	1.52	0.030	0.060	
Е	4.93	5.28	0.194	0.208	
F	0.051	0.203	0.002	0.008	
G	0.15	0.31	0.006	0.012	
Н	1.98	2.41	0.078	0.095	
J	6.50		0.256		
K		2.30		0.090	
L	1.70		0.067		

REEL SPECIFICATION

P/N	PKG	QTY
MURAXXXT3G-MS	DO-214AC(SMA)	2000



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